

Title (en)

A method of operating a MOS-structure and MOS-structure therefor.

Title (de)

Verfahren zum Betrieb einer MOS-Struktur und MOS-Struktur dafür.

Title (fr)

Procédé pour le fonctionnement d'une structure MOS et structure MOS dans ce but.

Publication

EP 0362961 A1 19900411 (EN)

Application

EP 89202497 A 19891003

Priority

NL 8802423 A 19881003

Abstract (en)

A SOI-nMOS-structure is cooled such that a charge is maintained in a cavity (5) of such structure for a long period of time. Applications comprise memory element.

IPC 1-7

H01L 29/66; **H01L 29/784**

IPC 8 full level

H01L 27/10 (2006.01); **H01L 27/12** (2006.01); **H01L 29/66** (2006.01); **H01L 29/78** (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP)

H01L 27/1203 (2013.01); **H01L 29/66992** (2013.01); **H01L 29/78648** (2013.01)

Citation (search report)

- [XD] EP 0207619 A1 19870107 - FUJITSU LTD [JP]
- [AD] EP 0114061 A2 19840725 - HITACHI LTD [JP]
- [XD] IEEE ELECTRON DEVICE LETTERS, vol. EDL-4, no. 8, August 1983, pages 269-271, IEEE; B.-Y. TSAUR et al.: "Fully isolated lateral bipolar-MOS transistors fabricated in zone-melting-recrystallized Si films on SiO₂"
- [XD] IEEE ELECTRON DEVICE LETTERS, vol. EDL-4, no. 6, June 1983, pages 193-195, IEEE; M. RODDER et al.: "Silicon-on-insulator bipolar transistors"
- [AD] IEEE TRANSACTIONS ON ELECTRON DEVICES, vol. ED-32, no. 2, February 1985, pages 258-281, IEEE; S.D.S. MALHI et al.: "Characteristics and three-dimensional integration of MOSFET's in small-grain LPCVD polycrystalline silicon"

Cited by

US9812179B2; US9012963B2; US9679612B2; WO2013026237A1; US10418091B2; US11031069B2; US10304837B2; US11081486B2

Designated contracting state (EPC)

AT BE CH DE ES FR GB GR IT LI LU NL SE

DOCDB simple family (publication)

EP 0362961 A1 19900411; **EP 0362961 B1 19940216**; AT E101753 T1 19940315; CA 1323942 C 19931102; DE 68913119 D1 19940324; DE 68913119 T2 19940526; ES 2049317 T3 19940416; JP H02150066 A 19900608; NL 8802423 A 19900501

DOCDB simple family (application)

EP 89202497 A 19891003; AT 89202497 T 19891003; CA 615003 A 19890929; DE 68913119 T 19891003; ES 89202497 T 19891003; JP 25865489 A 19891003; NL 8802423 A 19881003